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MBR830MFS, NRVB830MFS

SWITCHMODE Power Rectifiers

These state-of-the-art devices have the following features:

Features

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Wettable Flasks Option Available
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Mechanical Characteristics:

- Case: Epoxy, Molded
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	V
Average Rectified Forward Current (Rated V_R , $T_C = 143^\circ\text{C}$)	$I_{F(AV)}$	8.0	A
Peak Repetitive Forward Current, (Rated V_R , Square Wave, 20 kHz, $T_C = 143^\circ\text{C}$)	I_{FRM}	16	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Storage Temperature Range	T_{stg}	-65 to +150	°C
Operating Junction Temperature	T_J	-40 to +150	°C
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E_{AS}	100	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.


NOTE: The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dPD/dT_J < 1/R_{JA}$.

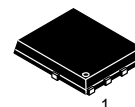


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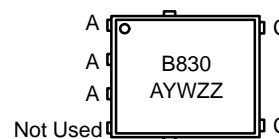
SCHOTTKY BARRIER RECTIFIERS 8 AMPERES 30 VOLTS

1,2,3  5,6



SO-8 FLAT LEAD
CASE 488AA
STYLE 2

MARKING DIAGRAM



B830 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
MBR830MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
MBR830MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NRVB830MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NRVB830MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case, Steady State (Assumes 600 mm ² 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JC}$	–	2.0	°C/W

ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) ($i_F = 8$ Amps, $T_J = 125^\circ\text{C}$) ($i_F = 8$ Amps, $T_J = 25^\circ\text{C}$)	V_F	0.44 0.50	0.57 0.70	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$)	i_R	15 0.020	50 0.200	mA

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

TYPICAL CHARACTERISTICS

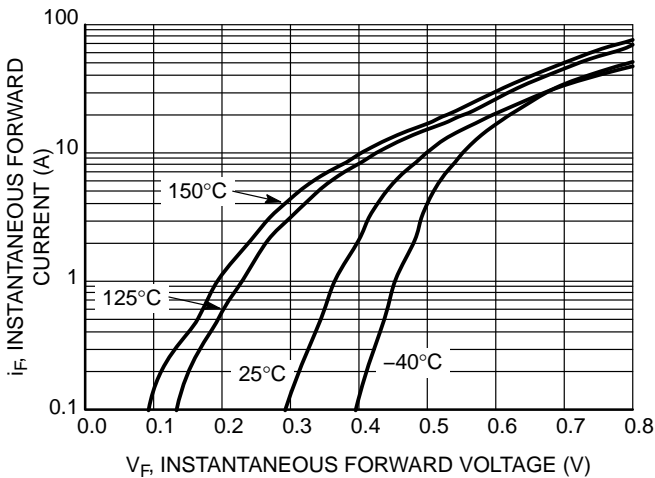


Figure 1. Typical Instantaneous Forward Characteristics

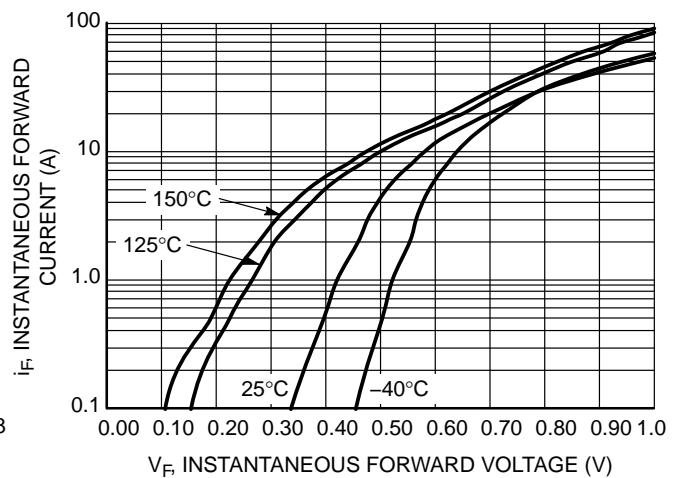


Figure 2. Maximum Instantaneous Forward Characteristics

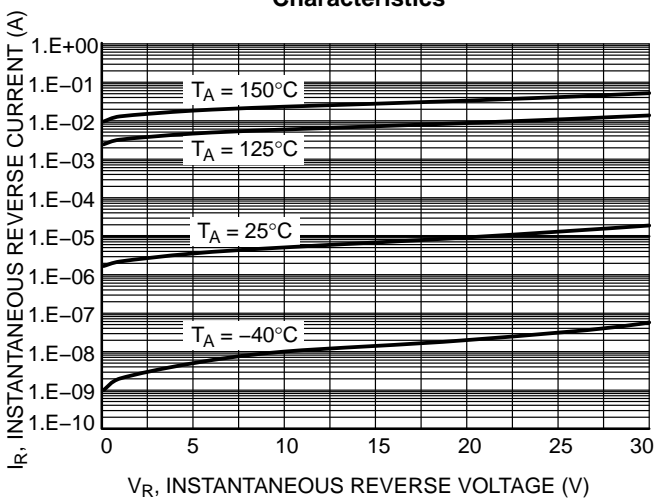


Figure 3. Typical Reverse Characteristics

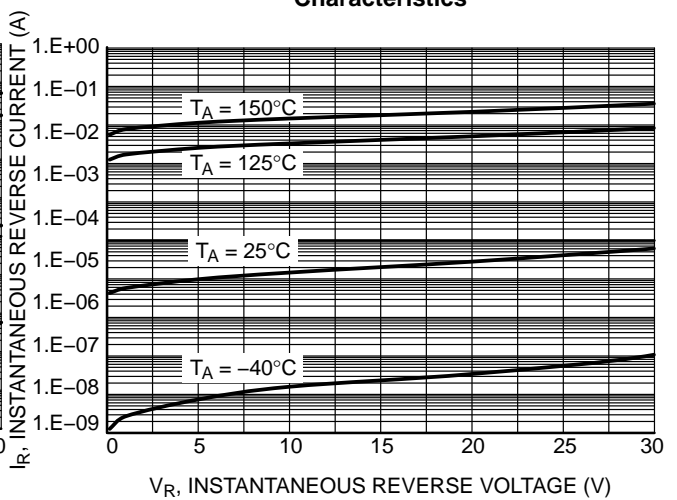


Figure 4. Maximum Reverse Characteristics

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TYPICAL CHARACTERISTICS

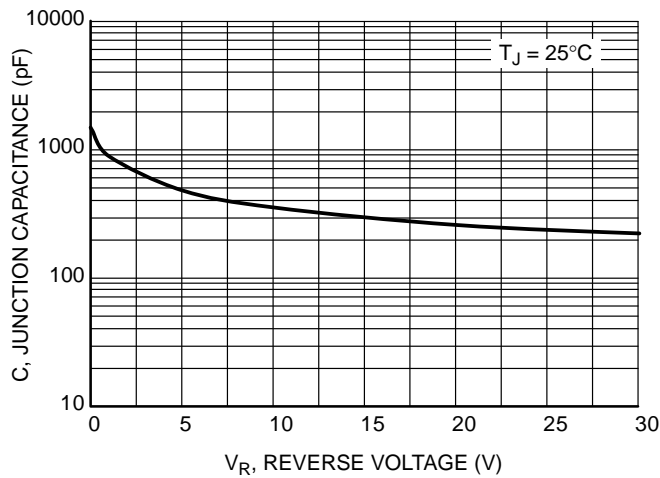


Figure 5. Typical Junction Capacitance

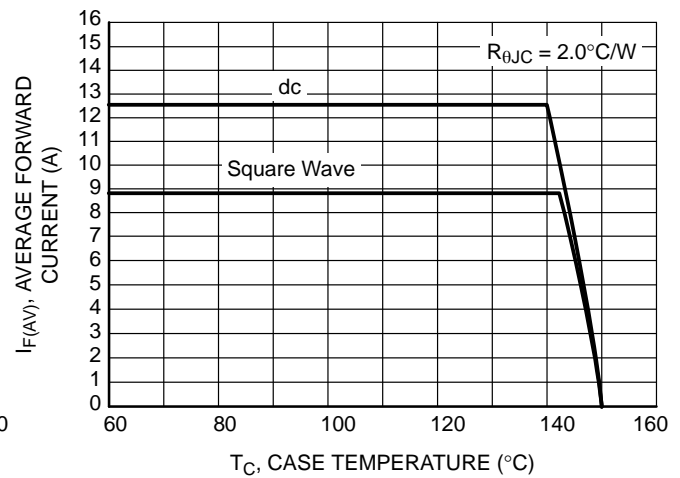


Figure 6. Current Derating TO-220AB

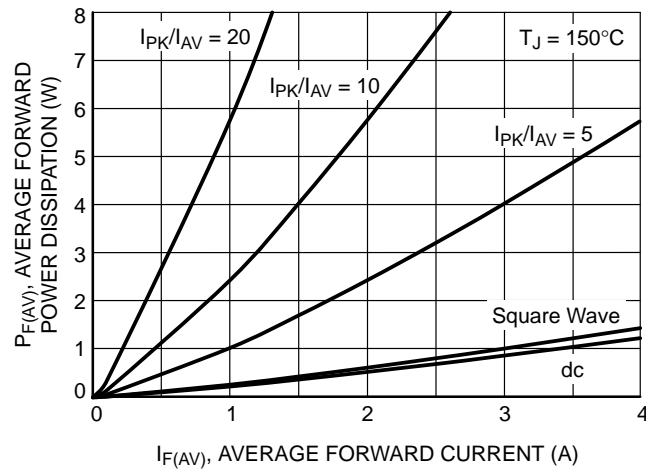


Figure 7. Forward Power Dissipation

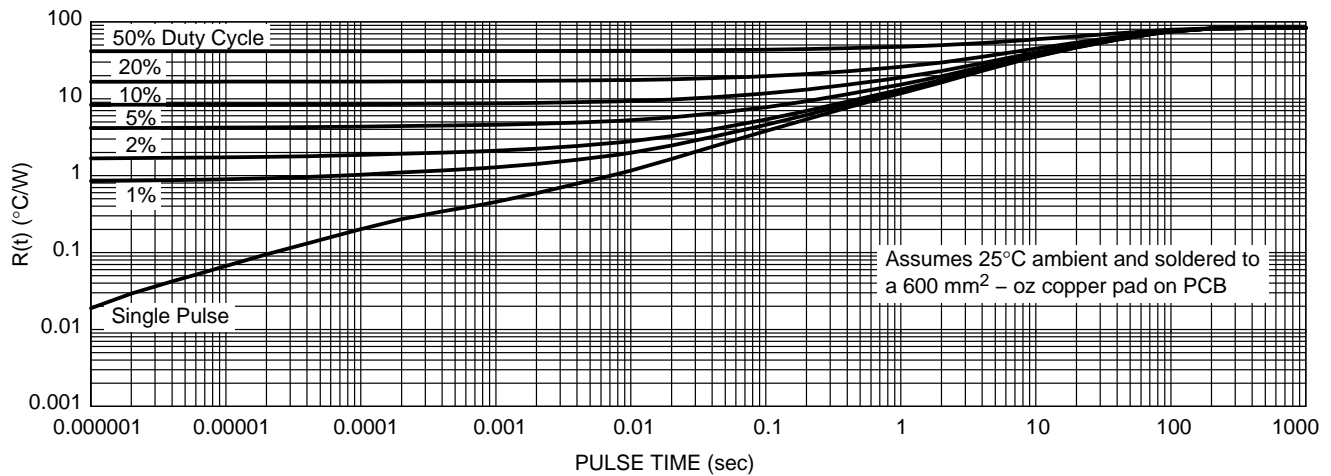


Figure 8. Thermal Response

